



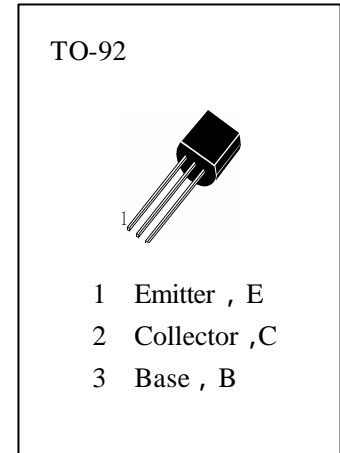
H128M

APPLICATIONS

Suitable For Low Voltage Large Current Drivers.

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg} —Storage Temperature.....	-55~150
T_j —Junction Temperature.....	150
P_C —Collector Dissipation.....	400mW
V_{CBO} —Collector-Base Voltage.....	20V
V_{CEO} —Collector-Emitter Voltage.....	15V
V_{EBO} —Emitter-Base Voltage.....	6.5V
I_C —Collector Current.....	1.5A



ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	20			V	$I_C=50 \mu A, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	15			V	$I_C=1 mA, I_B=0$
BVEBO	Emitter-Base Breakdown Voltage	6.5			V	$I_E=50 \mu A, I_C=0$
HFE	DC Current Gain	150				$V_{CE}=1V, I_C=100mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		0.2	0.3	V	$I_C=500mA, I_B=50mA$
ICBO	Collector Cut-off Current			0.1	μA	$V_{CB}=20V, I_E=0$
IEBO	Emitter Cut-off Current			0.1	μA	$V_{EB}=6V, I_C=0$
f _T	Current Gain-Bandwidth Product		260		MHz	$V_{CE}=5V, I_C=50mA$
Cob	Output Capacitance		5		pF	$V_{CB}=10V, I_E=0, f=1MHz$
Ron	On Resistance		0.6			$V_{IN}=0.3V, f=1KHz, I_B=1mA$